ECH8308-TL-H Datasheet

https://www.DiGi-Electronics.com

DiGi Electronics Part Number	ECH8308-TL-H-DG
Manufacturer	onsemi
Manufacturer Product Number	ECH8308-TL-H
Description	MOSFET P-CH 12V 10A 8ECH
Detailed Description	P-Channel 12 V 10A (Ta) 1.6W (Ta) Surface Mount 8-ECH

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
ECH8308-TL-H	onsemi
Series:	Product Status:
-	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
12 V	10A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
1.8V, 4.5V	12.5mOhm @ 5A, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
-	26 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±10V	2300 pF @ 6 V
FET Feature:	Power Dissipation (Max):
-	1.6W (Ta)
Operating Temperature:	Mounting Type:
150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
8-ECH	8-SMD, Flat Lead
Base Product Number:	
ECH8308	

Environmental & Export classification

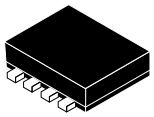
RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

DATA SHEET
www.onsemi.com

MOSFET – Power, P-Channel, Single ECH8

-12 V, -10 A, 12.5 mΩ

ECH8308

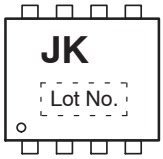


SOT−28FL / ECH8
CASE 318BF

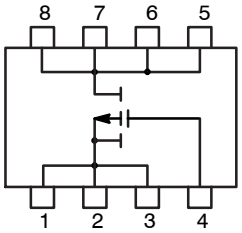
Features

- Best Suited for Load Switching
- 1.8 V Drive
- Protection Diode in
- Low ON−resistance
- This is a Pb−Free and Halide Free Device

MARKING DIAGRAM



ELECTRICAL CONNECTION



1: Source
2: Source
3: Source
4: Gate
5: Drain
6: Drain
7: Drain
8: Drain

ABSOLUTE MAXIMUM RATINGS (at Ta = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit
Drain−to−Source Voltage	V_{DSS}		−12	V
Gate−to−Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		−10	A
Drain Current (Pulse)	I_{DP}	PW ≤ 10 μs, duty cycle ≤ 1%	−40	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900 mm^2 × 0.8 mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

Device	Package	Shipping†
ECH8308−TL−H	SOT−28FL / ECH8 (Pb−Free and Halide Free)	3000 / Tape & Reel

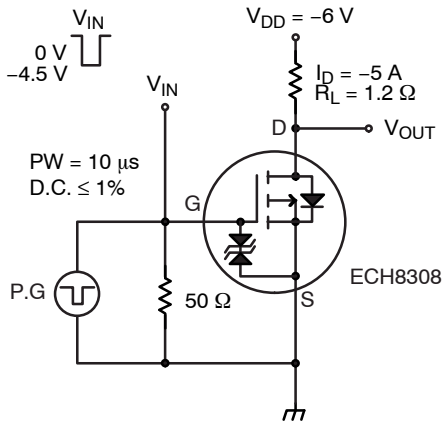
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (at Ta = 25°C)

Parameter	Symbol	Conditions	Ratings			Unit
			Min	Typ	Max	
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = −1 mA, V_{GS} = 0 V	−12	–	–	V
Zero−Gate Voltage Drain Current	I_{DSS}	V_{DS} = −12 V, V_{GS} = 0 V	–	–	−10	μA
Gate−to−Source Leakage Current	I_{GSS}	V_{GS} = ±8 V, V_{DS} = 0 V	–	–	±10	μA
Cutoff Voltage	$V_{GS(off)}$	V_{DS} = −6 V, I_D = −1 mA	−0.4	–	−1.3	V
Forward Transfer Admittance	| yfs |	V_{DS} = −6 V, I_D = −4.5 A	12	21	–	S
Static Drain−to−Source On−State Resistance	R_{DS}(on)1	I_D = −4.5 A, V_{GS} = −4.5 V	–	9.2	12.5	mΩ
	R_{DS}(on)2	I_D = −2 A, V_{GS} = −2.5 V	–	14	20	mΩ
	R_{DS}(on)3	I_D = −1 A, V_{GS} = −1.8 V	–	22	33	mΩ
Input Capacitance	Ciss	V_{DS} = −6 V, f = 1 MHz	–	2300	–	pF
Output Capacitance	Coss		–	720	–	pF
Reverse Transfer Capacitance	Crss		–	550	–	pF
Turn−ON Delay Time	t_d(on)	See specified Test Circuit.	–	24	–	ns
Rise Time	t_r		–	130	–	ns
Turn−OFF Delay Time	t_d(off)		–	230	–	ns
Fall Time	t_f		–	195	–	ns
Total Gate Charge	Qg	V_{DS} = −6 V, V_{GS} = −4.5 V, I_D = −10 A	–	26	–	nC
Gate−to−Source Charge	Qgs		–	4.0	–	nC
Gate−to−Drain “Miller” Charge	Qgd		–	7.1	–	nC
Diode Forward Voltage	V_{SD}	I_S = −10 A, V_{GS} = 0 V	–	−0.79	−1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit



ECH8308

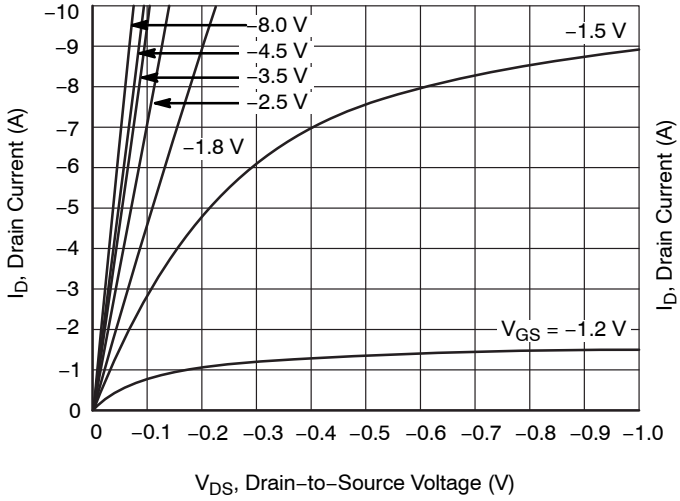


Figure 1. I_D – V_{DS}

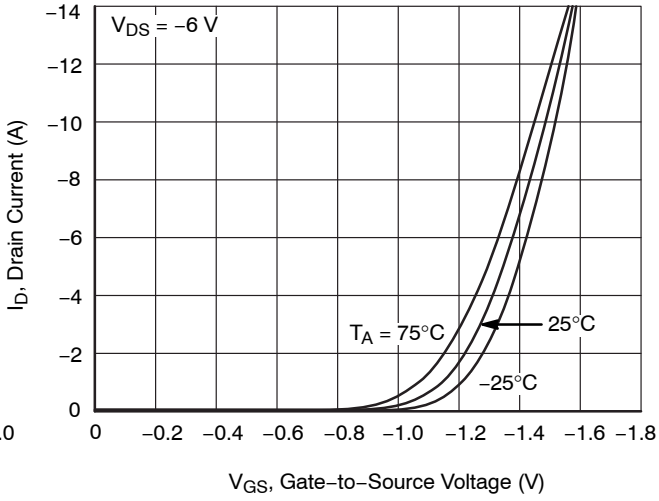


Figure 2. I_D – V_{GS}

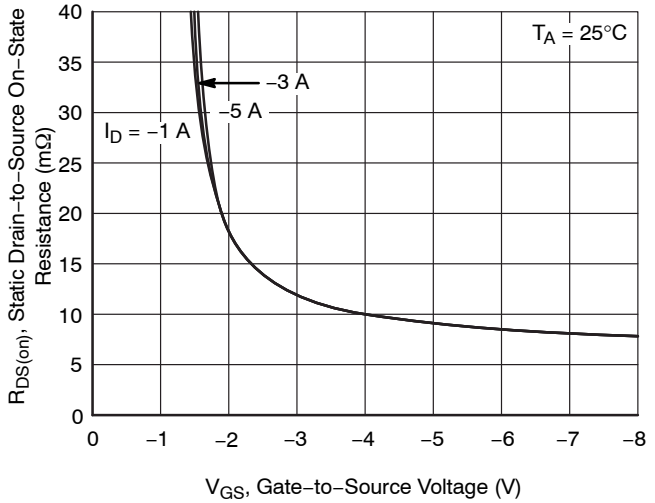


Figure 3. $R_{DS(on)}$ – V_{GS}

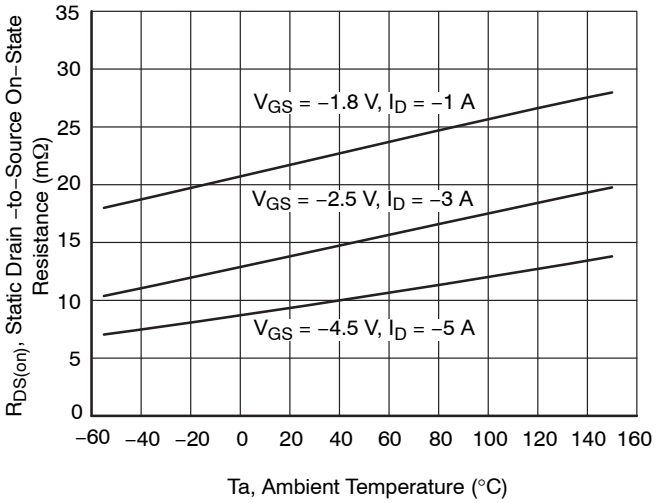


Figure 4. $R_{DS(on)}$ – Ta

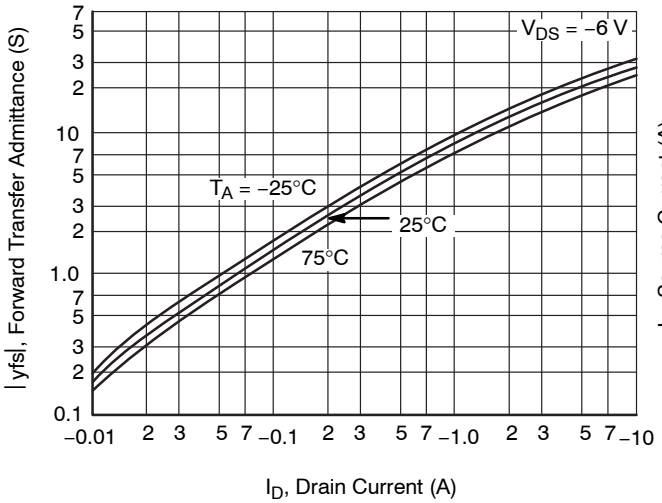


Figure 5. $|yfs|$ – I_D

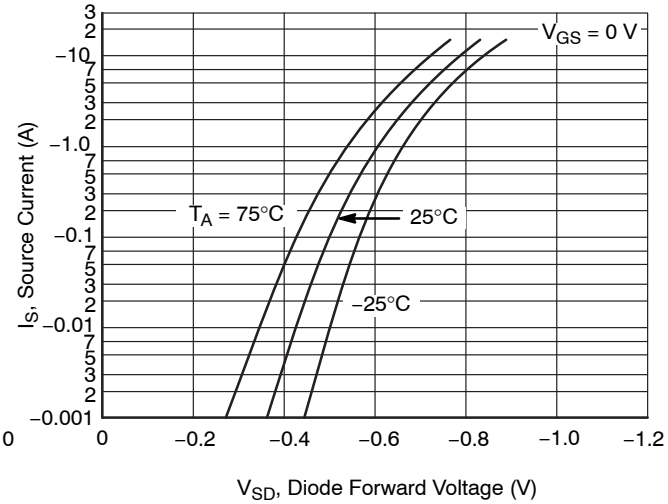


Figure 6. I_S – V_{SD}

ECH8308

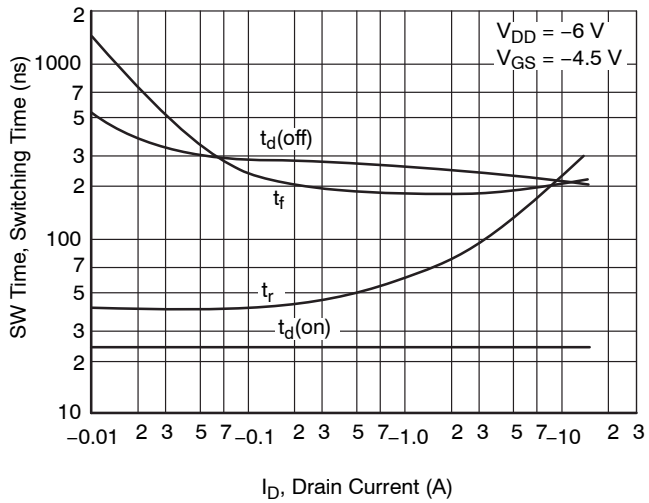


Figure 7. SW Time – I_D

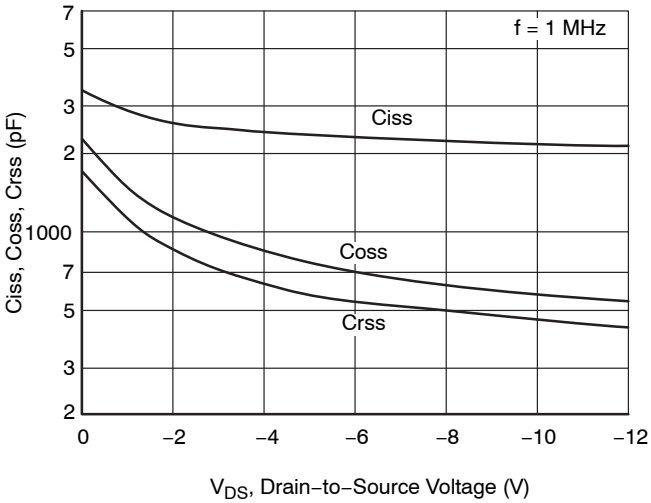


Figure 8. Ciss, Coss, Crss – V_{DS}

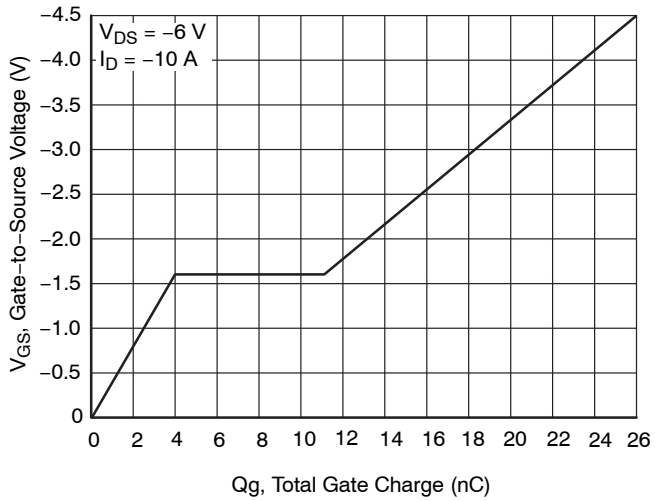


Figure 9. V_{GS} – Qg

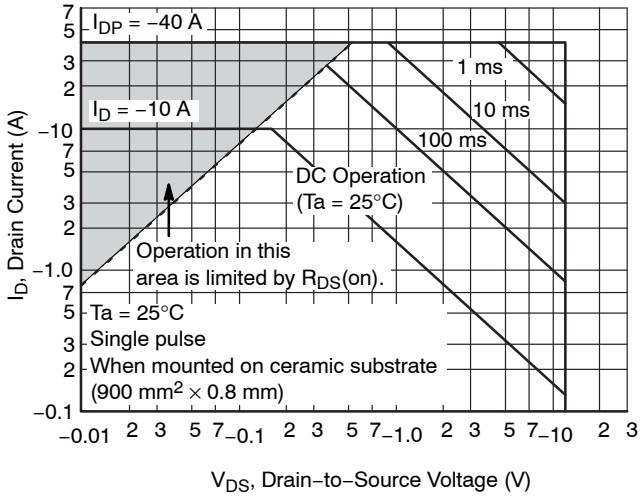


Figure 10. ASO

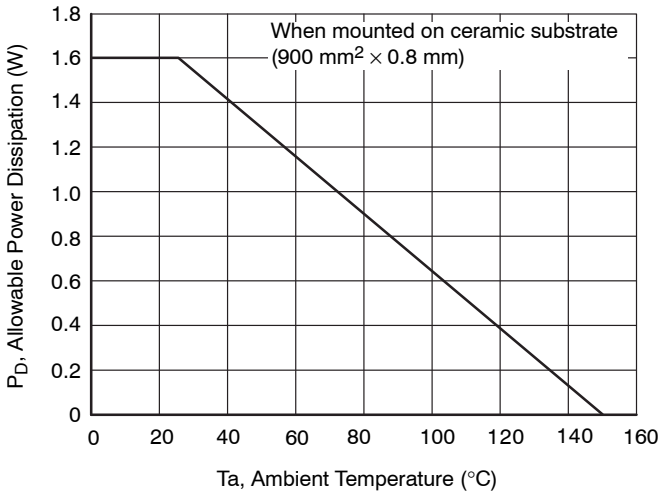


Figure 11. P_D – Ta

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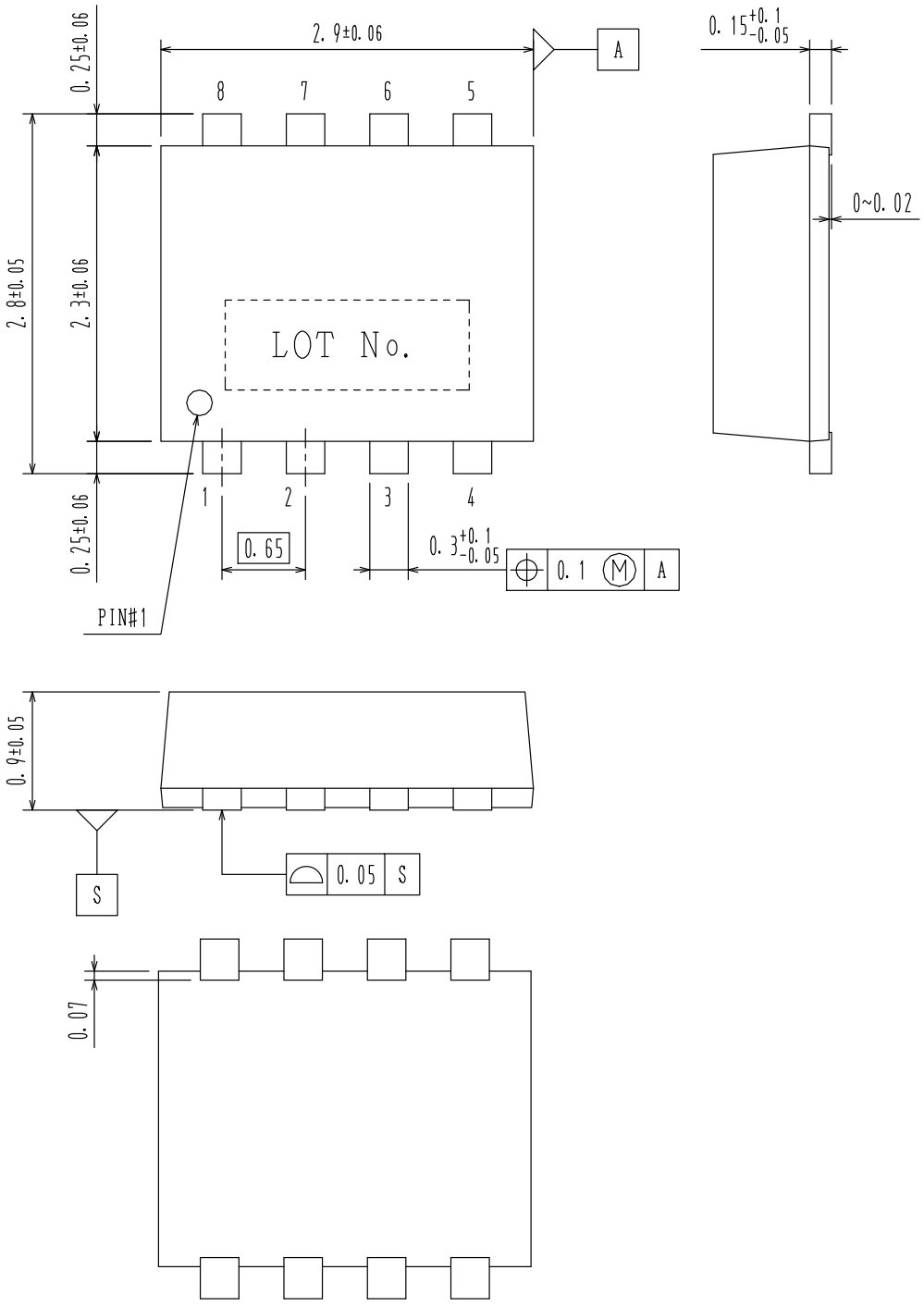
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

SOT−28FL / ECH8
CASE 318BF
ISSUE O

DATE 31 MAR 2012



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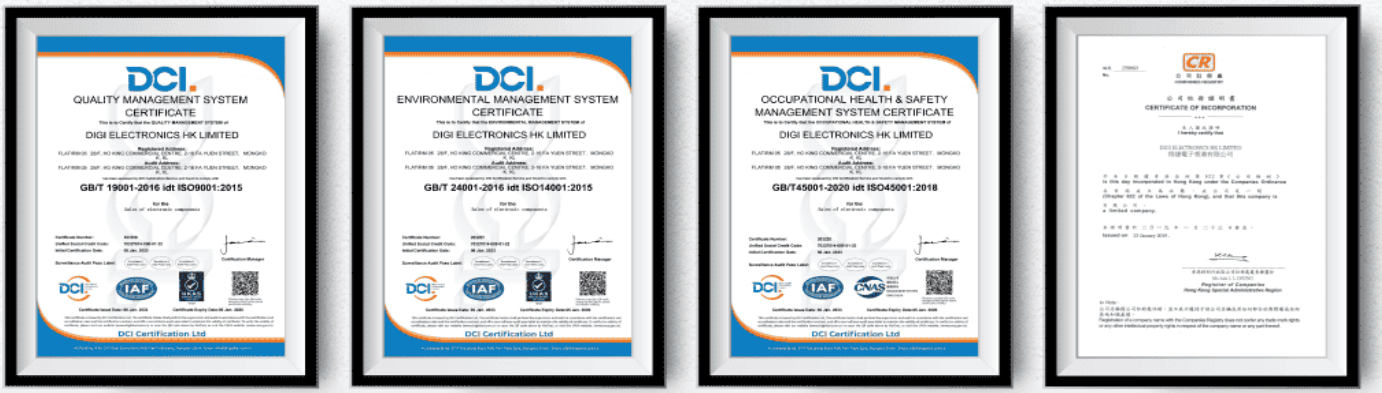

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